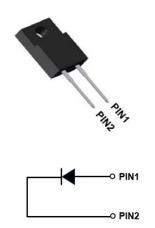




# Silicon Carbide Schottky Diode

$V_{RRM}$	1200V
I <sub>F (100°C)</sub>	8A
Qc	37nC



#### **Features**

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

### **Typical Applications**

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

### **Mechanical Data**

 Package: ITO-220AC
Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

# ■Maximum Ratings ( $T_C$ =25 $^{\circ}$ C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112008FQG3
Reverse voltage (Repetitive peak) @ T <sub>j</sub> =25°C	$V_{RRM}$	٧	1200
Reverse voltage (Surge peak) @ T <sub>j</sub> =25°C	$V_{RSM}$	V	1200
Reverse voltage (DC) @ T <sub>j</sub> =25°C	V <sub>DC</sub>	V	1200
Continuous forward current @ T <sub>C</sub> =25°C			12
Continuous forward current @ T <sub>C</sub> =100°C	I <sub>F</sub>	Α	8
Continuous forward current @ T <sub>C</sub> =135°C			5
Non-repetitive peak forward surge current @ T <sub>c</sub> =25°C, tp=10ms, Half Sine Wave	I <sub>FSM</sub>	А	95
Power Dissipation@ T <sub>C</sub> =25°C	Б	V	33
Power Dissipation@ T <sub>C</sub> =110°C	P <sub>TOT</sub>		14
i²t Value@ T <sub>C</sub> =25°C ,tp=10ms	∫ i²dt	A <sup>2</sup> S	45
Operating junction and Storage temperature range	$T_{j}$ , $T_{stg}$	°C	-55 to +175





### **■**Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V <sub>F</sub>	V	I <sub>F</sub> =8A, T <sub>j</sub> =25°C	1.46	1.55
			I <sub>F</sub> =8A, T <sub>j</sub> =175°C	2.2	-
Reverse leakage current I <sub>R</sub>	_	μА	V <sub>R</sub> =1200V, T <sub>j</sub> =25°C	1	10
	IR		V <sub>R</sub> =1200V, T <sub>j</sub> =175°C	5	-
Total capacitive charge	Q <sub>C</sub>	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{VR}C(V)dV$	37	-
Total capacitance	С	pF	V <sub>R</sub> =0V, f=1MHZ	500	-
			V <sub>R</sub> =400V, f=1MHZ	35	-
			V <sub>R</sub> =800V, f=1MHZ	27	-
Capacitance Stored Energy	Ec	μJ	V <sub>R</sub> =800V	9.5	-

## **■Thermal Characteristics** (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	R <sub>eJ-C</sub>	°C W	4.55

## **■**Typical Characteristics

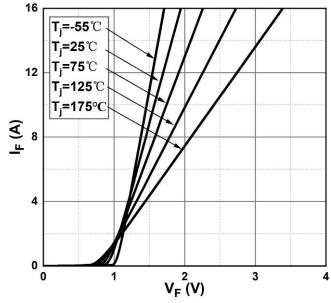


Figure 1. Forward Characteristics

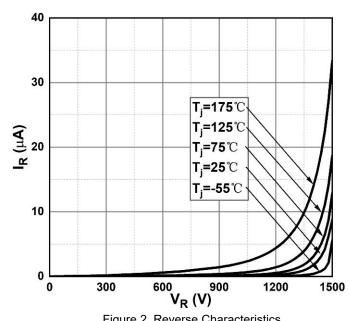
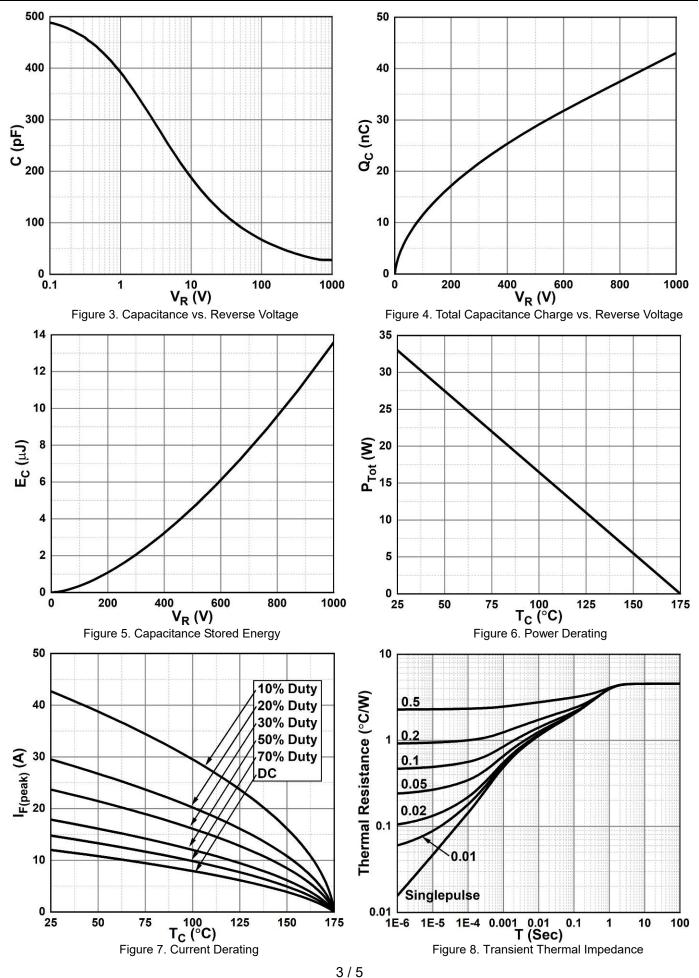


Figure 2. Reverse Characteristics



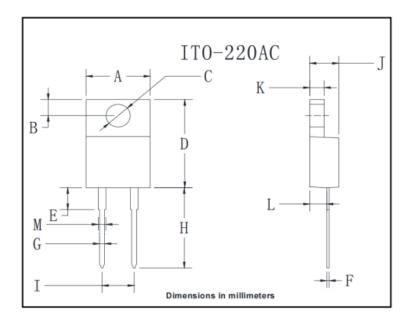








## **■**Outline Dimensions



ITO-220AC				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
E	3.5	4.1		
F	0.45	0.75		
G	0.45	0.75		
Н	13.35	14.15		
I	4.97	5.23		
J	4.3	4.8		
K	2.5	2.74		
L	2.58	2.82		
М	1.03	1.43		



## YJD112008FQG3



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